Table 2: NAND Gate Data

	$V_A$	$V_B$	$V_{DA}$	$V_{DB}$	$V_P$	$I_{R1}$	$I_{R2}$	$V_B$	$V_Y$
	(V)	(V)	(V)	(V)	(V)	(mA)	(mA)	(mV)	(V)
4	4.95	4.95	-3.11	-3.11	1.81	1.92	2.28	1.71	0,02
-	4.95	0	-4.43	0.5	0.5	2.01	0.03	0.01	4.93
	0	0	0.49	0.49	0.5	2.01	0.032	0.01	4.93
	0	4.95	0.60	-4.33	0.6	1.96	0.027	0.03	4.09

Table 3: Inverter Data

Input	Input	$V_P$	$V_B$	Output
A (V)	B (V)	(V)	(V)	Y (V)
9.95	0	0.5	0.01	4.93
4.95	4.95	1.81	0.71	0.02

 $\overline{Signature}$ 

## Report

Please answer the following questions briefly in the given space.

1. Using experimental data, find the operating mode of Q1 when input A is HIGH and input B is LOW. Additionally, find whether diodes DA and DB are ON or OFF (by using the voltage across them).

Here,  $I_E = 0 \text{ mA}$   $I_B = \frac{V_B - O}{19.45} = 0.01 \approx 0 \text{ mA}$   $I_C = I_{R_2} = 0.03 \approx 0 \text{ mA}$   $Q_1 \text{ is in cutoff mode}$   $G_1 \text{ by DB}$ 

A. 05V) DA V, D. DZ 31945 (A. 95V) DB

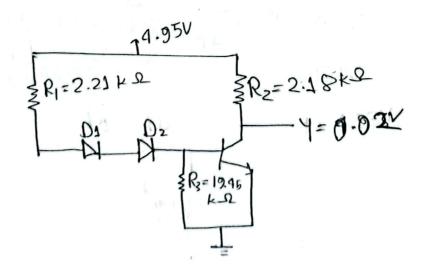
voltage on cathode > voltage in anode which mens DA is off

for DB, voltage in cathode Votage in anode, meaning DB is ON.

2. Assume that the output of the circuit shown in Fig. 1 is LOW. Draw the partial circuit consisting of only those components which remain active.

Ans.

In order to get Low output from this circuit, diodes DA and DB hartobe off. Therefore the active part of the circuit is drawn below.



3. What should be the relation between the currents  $I_{R1}$ ,  $I_B$  and  $I_{RB}$  when all inputs are HIGH? Did you obtain a similar result in your experiment? Explain briefly. (use a Multi-meter as Ammeter to measure  $I_B$ ).

Ans. 1.11 and 1.12 and 1.13 and 1.14 Ans. When all inputs are HIGH, dioded DA and DB are OFF while O1 and D2 areon. IRs can travel through and Dz and be divided into IB and IRB theoretically IRB = VB-0 = 0.7-0 = 0.035 mA .. IB = IRI-IRB = 1.42-0.035 = 1.385 mA

from the experiment, we get IRB = 0.71-0 mA = 0.037mA

-: Epoperimentally IB = IR1-IRB\* = 1.383 mA ... Theoretical IB is very close to experimental IB Because the IRI = IRB+ IB relation is The.

4. Use the relation between the currents  $I_{R1}$ ,  $I_{B}$  and  $I_{RB}$  when all inputs are HIGH to verify the operating

The experimental value of y when both of the inputs are high is 0.027. This suggests QI is in saturation mod

Here, Ie = IR2 = 2.28 mA IB = 1.383 mA Ic = 2.28 - 1.64 < BF

which verifies Hat Q1 is in caturation

60

Will the circuit still work properly as NAND gate if the diodes D<sub>1</sub> and D<sub>2</sub> are removed? Measure the output voltage for the four different cases and verify.

VA	VB	Vy
0	0	4.921
0	4.95	4,95
9.95	+ -	4.94
3	9.94	0.03
1	-	

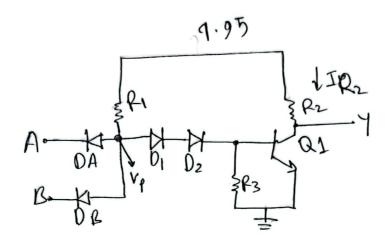
6. Vary the input A from 0V to 5V while keeping input B fixed at 5V. What is the maximum value of input A for which the output remains HIGH? [consider any voltage above 1V as HIGH]

Ans.

108 V is the maximum value of input A

for which the output remains HIGH

7. Verify the result of table 2 using theoretical calculation and comment on the result (Use extra page necessary).



Theoretically, when A and B are both high (1.05v), DA and DB should be OFF and Vp will be High, resulting in the transistor to be in saturation mode. Therefore, output should be LOW, VB should be near O-7 and Ie/O. All of these assumptions are proven two in the first row of Data Table 2.

When either of the inputs are low, Vp remains low resulting in the transistor to be in cutoff mode and the output to be High. Je, I = and IB should be nearo zero. These assumptions are also proven right in the 2nd and 9th row of Data Table 2.

finally if both of the inputs are low, that wold result in DA, DB ON, VP = LOW, Q1 is in saturation, author is High Also proven right in row 3 of the table.